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	Livello bibliografico	Monografia
2.	Record Nr.	UNISA996466822003316
	Autore	Grøn Øyvind
	Titolo	Lecture Notes on the General Theory of Relativity [[electronic resource]] : From Newton's Attractive Gravity to the Repulsive Gravity of Vacuum Energy / / by Øyvind Grøn
	Pubbl/distr/stampa	New York, NY : , : Springer New York : , : Imprint : Springer, , 2009
	ISBN	1-280-38477-8 9786613562692 0-387-88134-4
	Edizione	[1st ed. 2009.]
	Descrizione fisica	1 online resource (XII, 252 p. 93 illus.)
	Collana	Lecture Notes in Physics, , 0075-8450 ; ; 772
	Classificazione	530 UD 8220
	Disciplina	530.11
	Soggetti	Gravitation Physics Astronomy Astrophysics Classical and Quantum Gravitation, Relativity Theory Mathematical Methods in Physics Astronomy, Astrophysics and Cosmology
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Formato	Materiale a stampa
Livello bibliografico	Monografia
Note generali	Bibliographic Level Mode of Issuance: Monograph
Nota di bibliografia	Includes bibliographical references and index.
Nota di contenuto	Newton's Law of Universal Gravitation -- The Special Theory of Relativity -- Vectors, Tensors and Forms -- Accelerated Reference Frames -- Covariant Differentiation -- Curvature -- Einstein's Field Equations -- The Schwarzschild Spacetime -- Black Holes -- Schwarzschild's Interior Solution -- Cosmology.
Sommario/riassunto	This book has resulted from a course in the general theory of relativity at the University of Oslo where the author has lectured for more than twenty years. Although the text is designed for master students, it is rather self-contained. Since mathematics courses on differential geometry and tensor calculus usually employ a rather abstract notation different from the component notation used in physical applications, the book introduces not only an introduction to the physical principles of the theory and physical applications of the theory, but also introduces the mathematics which is needed, in particular the calculus of differential forms. Detailed calculations are given of the bending of light, the perihelion precession of Mercury and the predictions for the Hafele-Keating experiment. The Tolman-Oppenheimer-Volkoff equation is deduced and solved for an incompressible fluid to give the internal Schwarzschild solution. Rotating black holes are discussed. The Friedmann-Robertson-Walker universe models are deduced. Also the reader will become familiar with the Universe model which is now considered as the standard model of the universe; a flat model filled with vacuum energy and cold matter. The inflationary era at the first moment of the history of our universe is also discussed.

3. Record Nr.	UNINA9910715745703321
Titolo	Message from the President of the United States, in answer to a resolution of the Senate, relative to the assemblage of persons on Round Island, coast of Mississippi, during the summer of 1849. June 11, 1850. Read, and ordered to be printed
Pubbl/distr/stampa	[Washington, D.C.] : , : [publisher not identified], , 1850
Descrizione fisica	1 online resource (4 pages)
Collana	Senate executive document / 31st Congress, 1st session. Senate ; ; no. 55 [United States congressional serial set] ; ; [serial no. 561]
Altri autori (Persone)	TaylorZachary <1784-1850.>
Soggetti	Blockade Insurgency Military art and science Subversive activities Filibusters Legislative materials.
Lingua di pubblicazione	Inglese
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Note generali	Batch processed record: Metadata reviewed, not verified. Some fields updated by batch processes. FDLP item number not assigned.

4.	Record Nr.	UNINA9910906001303321
	Autore	Alberti, Luigi <giurista>
	Titolo	Servitù di elettrodotto : le leggi, la procedura, la giurisprudenza ... / Luigi Alberti
	Pubbl/distr/stampa	Milano, : Pirola, 1962
	Edizione	[3. ed.]
	Descrizione fisica	375 p. ; 24 cm
	Disciplina	347
	Locazione	DEC
	Collocazione	DPR 2 148
	Lingua di pubblicazione	Italiano
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5.	Record Nr.	UNINA9910958624203321
	Autore	Rohde Ulrich L
	Titolo	RF/microwave circuit design for wireless applications / / Ulrich L. Rohde, Matthias Rudolph
	Pubbl/distr/stampa	Hoboken, N.J., : Wiley, 2013
	ISBN	1-118-43140-5 1-283-85885-1 1-118-43148-0
	Edizione	[2nd ed.]
	Descrizione fisica	xix, 893 p. : ill
	Altri autori (Persone)	RudolphMatthias <1969->
	Disciplina	621.381/32
	Soggetti	Microwave circuits - Design and construction Microwave integrated circuits - Computer-aided design Radio frequency integrated circuits - Design and construction Semiconductors - Computer-aided design Wireless communication systems - Equipment and supplies - Design and construction
	Lingua di pubblicazione	Inglese
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Livello bibliografico	Monografia
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Nota di contenuto	RF/Microwave Circuit Design for Wireless Applications -- Contents -- Foreword -- Preface -- 1 Introduction to Wireless Circuit Design -- 1.1 Introduction -- 1.2 System Functions -- 1.3 The Radio Channel and Modulation Requirements -- 1.3.1 Introduction -- 1.3.2 Channel Impulse Response -- 1.3.3 Doppler Effect -- 1.3.4 Transfer Function -- 1.3.5 Time Response of Channel Impulse Response and Transfer Function -- 1.3.6 Lessons Learned -- 1.3.7 Wireless Signal Example: The TDMA System in GSM -- 1.3.7.1 Frequency Division Multiple Access (FDMA) -- 1.3.7.2 Time-Division Multiple Access (TDMA) -- 1.3.7.3 Code-Division Multiple Access (CDMA) -- 1.3.7.4 TDMA in GSM -- 1.3.7.5 TDMA Structure -- 1.3.7.6 Bit Synchronization -- 1.3.7.7 Compensation of Multipath Reception -- 1.3.8 From GSM to UMTS to LTE -- 1.4 About Bits, Symbols, and Waveforms -- 1.4.1 Introduction -- 1.4.1.1 Representation of a Modulated RF Carrier -- 1.4.1.2 The Spectrum of a Digitally Modulated Carrier -- 1.4.2 Some Fundamentals of Digital Modulation Techniques -- 1.4.2.1 Spread-Spectrum and CDMA Modulation Techniques -- 1.4.2.2 Orthogonal Frequency Division Modulation (OFDM) and Single-Carrier Frequency-Division Multiple Access (SC-FDMA) -- 1.5 Analysis of Wireless Systems -- 1.5.1 Analog and Digital Receiver Designs -- 1.5.1.1 Receiver Design Examples -- 1.5.1.2 PLL CAD Simulation -- 1.5.2 Transmitters -- 1.5.2.1 Linear Digital Modulation -- 1.5.2.2 Digital and Analog FM -- 1.5.2.3 Single Sideband AM (SSB-AM) -- 1.5.2.4 Designing with the SA900 -- 1.5.2.5 ISM Band Application -- 1.6 Building Blocks -- 1.7 System Specifications and Their Relationship to Circuit Design -- 1.7.1 System Noise and Noise Floor -- 1.7.2 System Amplitude and Phase Behavior -- 1.8 Testing -- 1.8.1 Introduction -- 1.8.2 Transmission and Reception Quality -- 1.8.3 Base Station Simulation -- 1.8.4 GSM. 1.8.5 DECT -- 1.9 Converting C/N or SNR to EB/N0 -- References -- Further Reading -- 2 Models for Active Devices -- 2.1 Diodes -- 2.1.1 Large-Signal Diode Model -- 2.1.2 Mixer and Detector Diodes -- 2.1.2.1 Junction Capacitance -- 2.1.2.2 Parameter Trade-Offs -- 2.1.2.3 Mixer Diodes -- 2.1.2.4 Linear Diode Model -- 2.1.3 PIN Diodes -- 2.1.3.1 Introduction -- 2.1.3.2 Large-Signal PIN Diode Model -- 2.1.3.3 Basic Theory: Variable Resistance -- 2.1.3.4 Breakdown Voltage, Capacitance, Q Factor -- 2.1.3.5 PIN Diode Applications -- 2.1.3.6 Example: A PIN Diode Network for TV Tuners -- 2.1.4 Tuning Diodes -- 2.1.4.1 Introduction -- 2.1.4.2 Tuning Diode Physics -- 2.1.4.3 Capacitance -- 2.1.4.4 Q Factor or Diode Loss -- 2.1.4.5 Distortion Products -- 2.1.4.6 Electrical Properties of Tuning Diodes -- 2.1.4.7 Diode-Tuned Resonant Circuits -- 2.2 Bipolar Transistors -- 2.2.1 Transistor Structure Types -- 2.2.2 Large-Signal Behavior of Bipolar Transistors -- 2.2.2.1 Electrical Characteristics and Specifications -- 2.2.3 Large-Signal Transistors in the Forward-Active Region -- 2.2.4 Improving RF Performance by Means of Heterostructures -- 2.2.5 Effects of Collector Voltage on Large-Signal Characteristics in the Forward-Active Region of BJTs -- 2.2.6 Effects of Collector Current and Voltage on Large-Signal Characteristics in the Forward-Active Region of HBTs -- 2.2.7 Saturation and Inverse Active Regions -- 2.2.8 Self-Heating -- 2.2.9 Small-Signal Models of Bipolar Transistors -- 2.3 Field-Effect Transistors -- 2.4 Large-Signal Behavior of JFETs -- 2.4.1 Small-Signal Behavior of JFETs -- 2.4.2 Large-Signal Behavior of MOSFETs -- 2.4.2.1 Transfer Characteristics of MOS Devices -- 2.4.2.2 MOS Device Voltage Limitations -- 2.4.3 Small-

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 5.3.1.4 Amplitude Stability -- 5.3.1.5 Phase Stability -- 5.4 Oscillator
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 5.5 Design of RF Oscillators -- 5.5.1 General Thoughts on Transistor
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 5.5.8.4 Tracking.

Sommario/riassunto

ULRICH L. ROHDE, PhD, Dr.-ing habil., is Chairman of Synergy
 Microwave Corporation; a partner of Rohde & Schwarz; and Professor of
 Microwave and RF Technology at the Brandenburgische Technische
 Universität Cottbus, Germany. He is a Fellow of the IEEE. MATTHIAS
 RUDOLPH, PhD, Dr.-ing, is the Ulrich L. Rohde Professor for RF and
 Microwave Techniques at Brandenburgische Technische Universität
 Cottbus, Germany. He worked previously at the Ferdinand-Braun-
 Institut, Leibniz-Institut für Höchstfrequenztechnik (FBH) in charge of
 GaAs semiconductor nonlinearity and noise modeling.